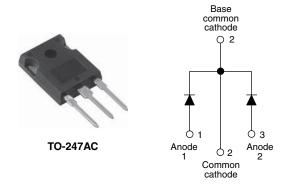


Vishay Semiconductors

HEXFRED® Ultrafast Soft Recovery Diode, 2 x 8 A



PRODUCT SUMMARY					
Package	TO-247AC				
I _{F(AV)}	2 x 8 A				
V_{R}	1200 V				
V _F at I _F	3.3 V				
t _{rr} (typ.)	28 ns				
T _J max.	150 °C				
Diode variation	Single die				

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified for industrial level





ITS

BENEFITS

- · Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA16PA120CPbF is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 8 A per leg continuous current, the VS-HFA16PA120CPbF is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16PA120CPbF is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V_{R}		1200	V		
Maximum continuous forward current	I_	T 100 °C	8			
per device	ce I _F	T _C = 100 °C	16	А		
Single pulse forward current	I _{FSM}		130	^		
Maximum repetitive forward current	I _{FRM}		32			
Maximum power discipation	В	T _C = 25 °C	73.5	W		
Maximum power dissipation	P_{D}	T _C = 100 °C	29] vv		
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C		

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ELECTRICAL SPECIFICATIONS PER LEG (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V _{BR}	Ι _R = 100 μΑ	1200	-	-		
		I _F = 8.0 A	-	2.6	3.3	V	
Maximum forward voltage	V_{FM}	I _F = 16 A	-	3.4	4.3		
		I _F = 8.0 A, T _J = 125 °C	-	2.4	3.1		
Maximum reverse		V _R = V _R rated	-	0.31	10		
leakage current		$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	-	135	1000	μA	
Junction capacitance	C _T	V _R = 200 V	-	11	20	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package	-	8.0	-	nH	

DYNAMIC RECOVERY CHARACTERISTICS PER LEG (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200$) A/μs, V _R = 30 V	-	28	-	ns	
Reverse recovery time	t _{rr1}	T _J = 25 °C		-	63	95		
	t _{rr2}	T _J = 125 °C	I _F = 8.0 A dI _F /dt = 200 A/µs	-	106	160		
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.5	8.0	A	
	I _{RRM2}	T _J = 125 °C		-	6.2	11		
Povorco rocovory chargo	Q_{rr1} $T_J = 25 ^{\circ}C$ $V = 200 ^{\circ}V$	$V_{\rm R} = 200 \text{ V}$	-	140	380	nC		
Reverse recovery charge	Q _{rr2}	T _J = 125 °C	H	-	335	880	110	
Peak rate of recovery current during t _b	dI _{(rec)M} /dt1	T _J = 25 °C		-	133	-	A/µs	
	dI _{(rec)M} /dt2	T _J = 125 °C		_	85	-	Ανμδ	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction to case	R _{thJC}		-	-	1.7		
Thermal resistance, junction to ambient	R _{thJA}	R _{thJA} Typical socket mount		-	40	K/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased		0.25	-		
Weight			-	6.0	-	g	
vveignt			-	0.21	-	OZ.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-247AC (JEDEC)		HFA16	PA120C		





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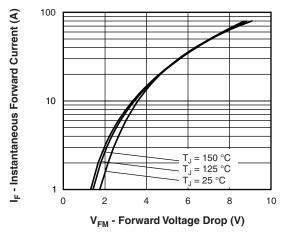


Fig. 1 - Maximum Forward Voltage Drop Characteristics

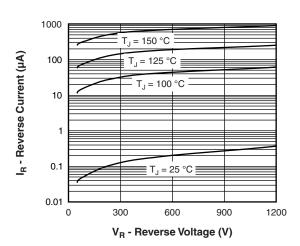


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

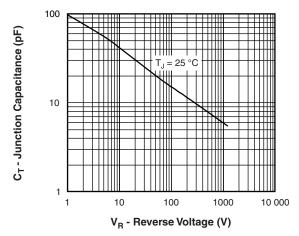


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

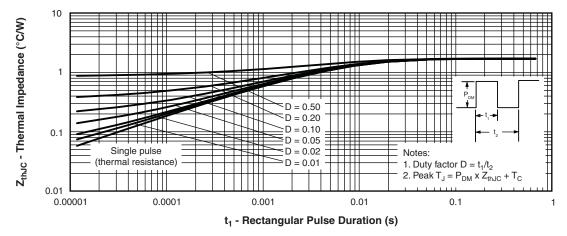


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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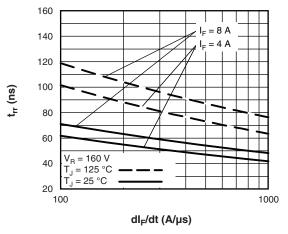


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

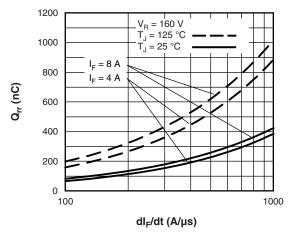


Fig. 7 - Typical Stored Charge vs. dl_F/dt

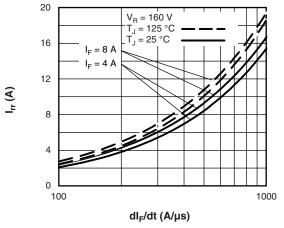


Fig. 6 - Typical Recovery Current vs. dl_F/dt

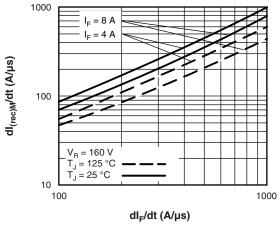


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt



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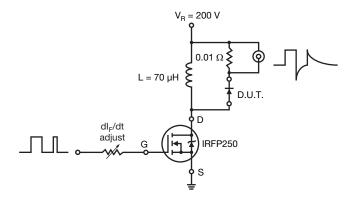
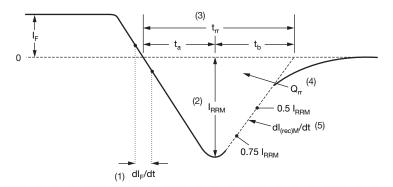


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $t_{\rm rr}$ reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

VS-HFA16PA120CPbF

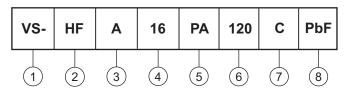
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ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

HEXFRED® family

Electron irradiated

Current rating (16 = 16 A)

PA = TO-247AC

Voltage rating: (120 = 1200 V)

Circuit configuration

C = Common cathode

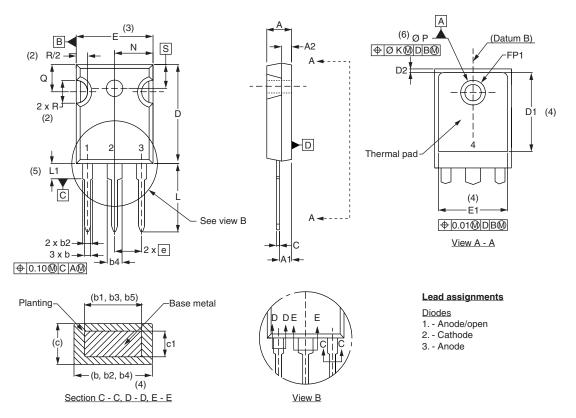
7 PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95223</u>					
Part marking information	www.vishay.com/doc?95226				



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DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	IETERS	INCHES		NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.37	0.065	0.094	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
С	0.38	0.86	0.015	0.034	
c1	0.38	0.76	0.015	0.030	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

SYMBOL	MILLIN	ILLIMETERS INCHES		NOTES	
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
E	15.29	15.87	0.602	0.625	3
E1	13.72	-	0.540	-	
е	5.46	BSC	0.215	BSC	
FK	2.	54	0.0	010	
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
N	7.62 BSC		0	.3	
ΦР	3.56	3.66	0.14	0.144	
ФР1	1	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	1.78	0.216	
S	5.51 BSC		0.217 BSC		

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c





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